

Title (en)

Active matrix type semiconductor display device

Title (de)

Halbleiteranzeigeeinrichtung mit aktiver Matrix

Title (fr)

Dispositif d'affichage à semi-conducteurs du type à matrice active

Publication

EP 1003151 A3 20011121 (EN)

Application

EP 99122790 A 19991116

Priority

- JP 32647098 A 19981117
- JP 8620299 A 19990329

Abstract (en)

[origin: EP1003151A2] There is provided an active matrix type semiconductor display device which realizes low power consumption and high reliability. In the active matrix type semiconductor display device of the present invention, a counter electrode is divided into two, different potentials are applied to the two counter electrodes, respectively and inversion driving is carried out each other. Since a potential of an image signal can be made low by doing so, it is possible to lower a voltage necessary for operation of a driver circuit. As a result, it is possible to realize improvement of reliability of an element such as a TFT and reduction of consumed electric power. Moreover, since it is possible to lower a voltage of a timing pulse supplied by the driver circuit, a booster circuit can be omitted, and reduction of an area of the driver circuit can be realized. <IMAGE>

IPC 1-7

G09G 3/36; **G09G 3/30**; **G09G 3/32**

IPC 8 full level

G09G 3/32 (2006.01); **G09G 3/36** (2006.01)

CPC (source: EP US)

G09G 3/3233 (2013.01 - EP US); **G09G 3/3655** (2013.01 - EP US); **H01L 27/12** (2013.01 - EP US); **H01L 27/1277** (2013.01 - EP US); **G02F 1/134318** (2021.01 - EP US); **G09G 3/3225** (2013.01 - EP US); **G09G 3/3614** (2013.01 - EP US); **G09G 2300/0465** (2013.01 - EP US); **G09G 2300/0842** (2013.01 - EP US); **G09G 2310/0254** (2013.01 - EP US); **G09G 2310/0262** (2013.01 - EP US); **G09G 2330/021** (2013.01 - EP US)

Citation (search report)

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Designated contracting state (EPC)

AT BE CH CY DE DK ES FI FR GB GR IE IT LI LU MC NL PT SE

DOCDB simple family (publication)

EP 1003151 A2 20000524; **EP 1003151 A3 20011121**; **EP 1003151 B1 20130821**; EP 2290643 A1 20110302; US 2003064552 A1 20030403; US 2004115851 A1 20040617; US 2007166860 A1 20070719; US 6489952 B1 20021203; US 6635505 B2 20031021; US 7198967 B2 20070403; US 7544981 B2 20090609

DOCDB simple family (application)

EP 99122790 A 19991116; EP 10010384 A 19991116; US 29588602 A 20021118; US 43843299 A 19991112; US 61885003 A 20030715; US 71593807 A 20070309